

DESCRIPTION

This "fast recovery" rectifier diode series is military qualified to MIL-PRF-19500/429 and is ideal for high-reliability applications where a failure cannot be tolerated. These industry-recognized 1.0 Amp rated rectifiers for working peak reverse voltages from 200 to 1000 volts are hermetically sealed with voidless-glass construction using an internal "Category I" metallurgical bond. These devices are also available in surface mount MELF package configurations by adding a "US" suffix (see separate data sheet for 1N5615US thru 1N5623US). Microsemi also offers numerous other rectifier products to meet higher and lower current ratings with various recovery time speed requirements including fast and ultrafast device types in both through-hole and surface mount packages.

IMPORTANT: For the most current data, consult MICROSEMI's website: <http://www.microsemi.com>

APPEARANCE

"A" Package
FEATURES

- Popular JEDEC registered 1N5615 to 1N5623 series
- Voidless hermetically sealed glass package
- Triple-Layer Passivation
- Internal "Category I" Metallurgical bonds
- Working Peak Reverse Voltage 200 to 1000 Volts.
- JAN, JANTX, JANTXV, and JANS available per MIL-PRF-19500/429
- Surface mount equivalents also available in a square end-cap MELF configuration with "US" suffix (see separate data sheet for 1N5615US thru 1N5623US)

APPLICATIONS / BENEFITS

- Fast recovery 1 Amp rectifiers 200 to 1000 V
- Military and other high-reliability applications
- General rectifier applications including bridges, half-bridges, catch diodes, etc.
- High forward surge current capability
- Extremely robust construction
- Low thermal resistance
- Controlled avalanche with peak reverse power capability
- Inherently radiation hard as described in Microsemi MicroNote 050

MAXIMUM RATINGS

- Junction & Storage Temperature: -65°C to +175°C
- Thermal Resistance: 38°C/W junction to lead at 3/8 inch (10 mm) lead length from body
- Thermal Impedance: 4.5°C/W @ 10 ms heating time
- Average Rectified Forward Current (I_O): 1.0 Amps @ $T_A = 55^\circ\text{C}$
- Forward Surge Current: 30 Amps @ 8.3 ms half-sine
- Solder Temperatures: 260°C for 10 s (maximum)

MECHANICAL AND PACKAGING

- CASE: Hermetically sealed voidless hard glass with Tungsten slugs (package dimensions on last page)
- TERMINATIONS: Axial leads are copper with Tin/Lead (Sn/Pb) finish. Note: Previous inventory had solid Silver axial-leads and no finish.
- MARKING: Body paint and part number, etc.
- POLARITY: Cathode band
- TAPE & REEL option: Standard per EIA-296
- WEIGHT: 340 mg

ELECTRICAL CHARACTERISTICS

TYPE	WORKING PEAK REVERSE VOLTAGE V_{RWM}	MINIMUM BREAKDOWN VOLTAGE V_{BR} @ 50 μ A	AVERAGE RECTIFIED CURRENT I_O @ T_A (NOTE 1)		FORWARD VOLTAGE (MAX.) V_F @ 3A	REVERSE CURRENT (MAX.) I_R @ V_{RWM}		CAPACITANCE (MAX.) C @ $V_R = 12$ V f=1 MHz	MAXIMUM SURGE CURRENT I_{FSM} (NOTE 2)	REVERSE RECOVERY (MAX.) (NOTE 3) t_{rr}
	VOLTS	VOLTS	AMPS		VOLTS	μ A		pF	AMPS	ns
			50°C	100°C		25°C	100°C			
1N5615	200	220	1.00	.750	.8 MIN.	.5	25	45	25	150
1N5617	400	440	1.00	.750		.5	25	35	25	150
1N5619	600	660	1.00	.750		.5	25	25	25	250
1N5621	800	880	1.00	.750	1.6	.5	25	20	25	300
1N5623	1000	1100	1.00	.750	MAX.	.5	25	15	25	500

NOTE 1: From 1 Amp at $T_A = 55^\circ\text{C}$, derate linearly at 5.56 mA/ $^\circ\text{C}$ to 0.75 Amp at $T_A = 100^\circ\text{C}$. From $T_A = 100^\circ\text{C}$, derate linearly at 7.5 mA/ $^\circ\text{C}$ to 0 Amps at $T_A = 200^\circ\text{C}$. These ambient ratings are for PC boards where thermal resistance from mounting point to ambient is sufficiently controlled where $T_{J(max)}$ does not exceed 175°C .

NOTE 2: $T_A = 100^\circ\text{C}$, f = 60 Hz, $I_O = 750$ mA for ten 8.3 ms surges @ 1 minute intervals

NOTE 3: $I_F = 0.5$ A, $I_{RM} = 1$ A, $I_{R(REC)} = 0.250$ A

SYMBOLS & DEFINITIONS

Symbol	Definition
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range
I_O	Average Rectified Output Current: Output Current averaged over a full cycle with a 50 hZ or 60 Hz sine-wave input and a 180 degree conduction angle
V_F	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current
I_R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature
C	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage
t_{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs.

GRAPHS

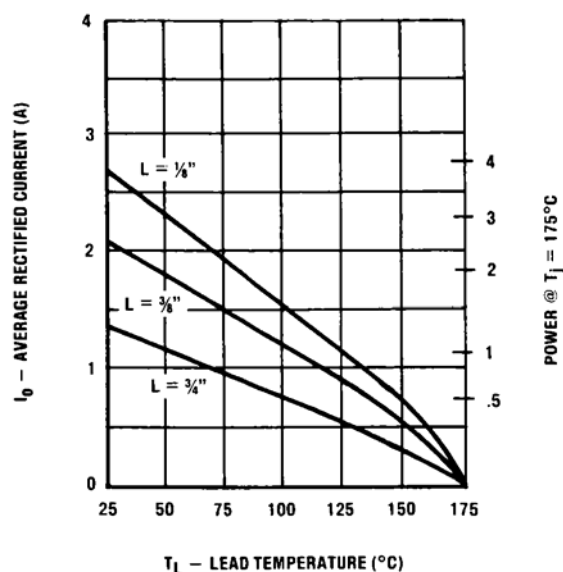


FIGURE 1
MAXIMUM CURRENT vs LEAD TEMPERATURE

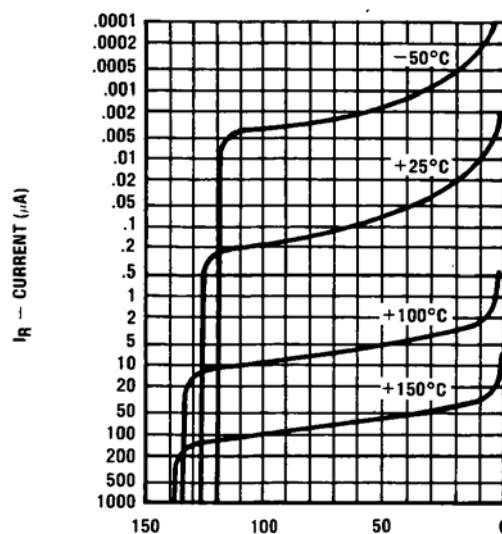


FIGURE 2
TYPICAL REVERSE CURRENT vs PIV



FIGURE 3

MAXIMUM POWER vs LEAD TEMPERATURE



FIGURE 4

TYPICAL FORWARD VOLTAGE vs FORWARD CURRENT

PACKAGE DIMENSIONS



Dimensions: Inches/[mm]

NOTE: Lead tolerance = +0.003/-0.004 inches

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Microchip:

[JANTXV1N5615/TR](#) [JANS1N5621/TR](#) [JANTXV1N5623/TR](#) [JAN1N5617/TR](#) [JANTX1N5621/TR](#) [JANTXV1N5619/TR](#)
[JANTX1N5623/TR](#) [JANTX1N5617/TR](#) [JANS1N5617/TR](#) [JAN1N5621/TR](#) [JAN1N5615/TR](#) [JANTXV1N5617/TR](#)
[JANTXV1N5621/TR](#) [JANTX1N5615/TR](#) [JANTX1N5619/TR](#) [JAN1N5623/TR](#) [JANS1N5615/TR](#) [JAN1N5619/TR](#)
[1N5617/TR](#) [1N5615E3](#) [1N5615/TR](#) [1N5615E3/TR](#) [1N5617e3/TR](#) [1N5623/TR](#) [1N5619/TR](#) [1N5623E3](#)
[1N5623E3/TR](#) [JAN1N5615](#) [JAN1N5619](#) [JAN1N5617](#) [JANS1N5615](#)

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9